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static electricity so as not to concentrate on a particular point, the particular point breakage can be prevented, and because the ESD protection circuit of the present invention has a BJT gain greater than the related art ESD protection circuit having resistors connected both to the emitter/the collector, an ESD protection capability is improved.

In the Claims:

Please amend the claims as follows:

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Sub D1
1. (Amended) An ESC (Electro-Static-Discharge) protection circuit comprising:
a pad and a main chip; and,
a plurality of transistors, each connected between the pad and the main chip, said transistors having a plurality of resistors connected to an input terminal, said resistors being connected in parallel with each other, and having no resistor connected between said transistors and ground.

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3. (Amended) A method for fabricating an ESD protection circuit, comprising the steps of:

(1) forming a transistor on a substrate;

(2) forming a first insulating film on the substrate inclusive of the

transistor and having a first contact hole to an input terminal of the transistor;

(3) forming a buffered layer in the first contact hole and the first insulating film in the vicinity of the first contact hole;

B8 (4) forming a second insulating film on the first insulating film inclusive of the buffered layer and having a second contact hole to the buffered layer; and,

(5) forming a pad both on the second contact hole and the second insulating film in the vicinity of the second contact hole.

Please add new claims as follows:

6. (New) An ESC (Electro-Static-Discharge) protection circuit comprising:

B9 Sub D2 a pad and a main chip, said chip comprising more than one discrete component; and

a plurality of transistors, each connected between the pad and the main chip, having resistors connected to an input terminal only.
